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FORESEE eMMC FEMDNN032G-A3A55 Datasheet

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Revision History:

Rev.	Date	Changes	Remark
1.0	2021/2/22	Basic spec and architecture	Target
1.1	2021/3/16	Change RPMB=16MB	
1.2	2021/5/17	Update drawing of product size.	
1.2	2021/3/17	From: 8. Package Dimension	
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1. Introduction

FORESEE eMMC is an embedded storage solution designed in the BGA package. The FORESEE eMMC consists of NAND flash and eMMC controller. The controller could manage the interface protocols, wear-leveling, bad block management and ECC. FORESEE eMMC has high performance at a competitive cost, high quality and low power consumption, and eMMC is compatible with JEDEC standard eMMC 5.1 specifications.

2. Product List

2. Prod	luct List		Longsys				
Density	Part Number	Capacity (MB)	Capacity (Bytes)	User Density(%)	Package Size(mm)	Package Type	
32GB	FEMDNN032G-A3A55	29600	31,037,849,600	90	11.5x13x0.8	153FBGA	

3. Features

> eMMC5.1 specification compatibility

(Backward compatible to eMMC4.41/4.5/5.0)

- Bus mode
 - Data bus width: 1 bit (default), 4 bits, 8 bits
 - Data transfer rate: up to 400MB/s (HS400)
 - MMC I/F Clock frequency : 0~200MHz
- Operating voltage range
 - Vcc(NAND): 2.7 3.6V
 - Vccq(Controller): 1.7 1.95V / 2.7 3.6V
- Temperature
 - Operation (-25°C ~ +85°C)
 - Storage without operation (-40 °C \sim +85 °C)
- Sudden-Power-Loss safeguard
- Hardware ECC engine
- Unique firmware backup mechanism

- Global-wear-leveling
- Supported features.
 - HS400, HS200
 - Partitioning, RPMB
 - Boot feature, boot partition
 - HW Reset/SW Reset
 - Discard, Trim, Erase, Sanitize
 - Background operations, HPI
 - Enhanced reliable write
 - S.M.A.R.T. Health Report
 - **FFU**
 - Sleep / awake
- Others
 - Compliance with the RoHS Directive

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4. Functional Description

FORESEE eMMC with powerful L2P (Logical to Physical) NAND Flash management algorithm provides unique functions:

- ➤ Host independence from details of operating NAND flash
- Internal ECC to correct defect in NAND flash
- Sudden-Power-Loss safeguard

To prevent from data loss, a mechanism named Sudden-Power-Loss safeguard is added in the eMMC. In the case of sudden power-failure, the eMMC would work properly after power cycling.

➤ Global-wear-leveling

To achieve the best stability and device endurance, this eMMC equips the Global Wear Leveling algorithm. It ensures that not only normal area, but also the frequently accessed area, such as FAT, would be programmed and erased evenly.

➤ IDA(Initial Data Acceleration)

The eMMC prevents the pre-burned data from data-loss with IDA, in case of our customer had pre-burned data to eMMC, before the eMMC being SMT.

> Cache

The eMMC enhanced the data written performance with Cache, with which our customer would get more endurance and reliability.

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5. Product Specifications

5.1 Performance

Density	Read	Turbo Write(FBA)
32GB	270MB/s	Up to 200MB/s

• Test Condition: Bus width x8, 200MHz DDR, 512KB data transfer, w/o file system overhead, measured on internal board

• Test tool: uBOOT (Without O/S)

• Test tool: CrystalDiskMark 6.0.0

• Test area: 1GB



5.2 Power Consumption

5.2.1 Active power consumption during operation

Density	Icc	Iccq		
32GB	100mA	140mA		

Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25°C.

• Vcc:3.3V & Vccq: 1.8V.

• The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

5.2.2 Low power mode (stand-by)

Density	Icc	Iccq 25
32GB	80uA	100uA

• Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25 °C.

• Vcc:3.3V & Vccq: 1.8V.

• Standby: Nand Vcc & Controller Vccq power supply is switched on.

Longsys • The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

5.2.3 Low power mode (sleep)

Density	Icc	Iccq
32GB	0	100uA

• Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25 $^{\circ}$ C.

• Vcc:3.3V & Vccq: 1.8V.

• Sleep: Nand Vcc power supply is switched off(Controller Vccq on)

• The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

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6. Pin Assignments

6.1 Ball Array view

		1	2	3	4	5	6	7	8	9	10	11	12	13	14	
	Α	NC	NC	DAT0	DATI	DAT2	Vss	RFU	NC	NC	NC	NC	NC	NC	NC	
	В	NC	DAT3	DAT4	DAT5	DAT6	DAT7	NC	NC	NC	NC	NC	NC	NC	NC	
	С	NC	(VDDi)	NC	Vssq	(NC)	Vccq	(NC)	(NC)	(NC)	NC	(NC)	(NC)	(NC)	NC	
	D	NC	NC	NC	NC					PQ1	110		NC	NC	NC	
	E	NC	(NC)	(NC)		RFU	Vcc	Vss	VSF	VSF	VSF		(NC)	(NC)	NC	
	F	NC	NC	NC		Vcc					VSF		NC	NC	NC	
100	tea)	NC	NC	RFU		Vss					VSF		NC	NC	NC	
Confider	н	NC	NC	NC		DS					Vss		NC	NC	NC	
	J	NC	NC	NC		vss					Vcc		NC	NC	NC	
	к	NC	(NC)	NC		RSTN	RFU	RFU	Vss	Vcc	VSF		(NC)	NC	NC	
	L	NC	NC	NC									NC	NC	NC	
	м	NC	NC	NC	Vccq	CMD	(CLK)	NC	NC	(NC)	NC	NC	NC	(NC)	(NC)	
	N	NC	Vssq	(NC)	Vccq	Vssq	(NC)	(NC)	(NC)	NC	NC	(NC)	(NC)	NC	NC	
	Р	NC	NC	Vccq	Vssq	Vccq	Vssq	(NC)	(NC)	NC	VSF	NC	NC	NC	NC	
				1												

FBGA153 - Ball Array (Ball side down view)

Signal	Description
CLOCK(CLK)	Each cycle of the clock directs a transfer on the command line and on the data lines.
	This signal is a bidirectional command channel used for device initialization and command transfer.
COMMAND(CMD)	The CMD Signal has 2 operation modes: open drain, for initialization, and push-pull, for command transfer.
Coy	Commands are sent from the host to the device, and responses are sent from the device to the host.
	These are bidirectional data signal. The DAT signals operate in push-pull mode.
	By default, after power-up or RESET, only DAT0 is used for data transfer. The controller can configure
	a wider data bus for data transfer wither using DAT [3:0](4bit mode)or DAT[7:0](8bit mode).
DATA(DAT0-DAT7)	Includes internal pull-up resistors for data lines DAT[7:1].Immediately after entering the 4-bit mode,
	the device disconnects the internal pull-up resistors on the DAT1 and DAT2 lines. (The DAT3 line internal pull-up is left connected.) Upon entering the 8bit mode, the device disconnects the internal pull-up on the DAT1, DAT2, and DAT[7:4] lines.
Data Straha(DS)	Newly assigned pin for HS400 mode. Data Strobe is generated from e.MMC to host.
Data Strobe(DS)	In HS400 mode, read data and CRC response are synchronized with Data Strobe.
RESET(RSTN)	Hardware Reset Input
Vccq	Vccq is the power supply line for host interface, have two power mode: High power mode: 2.7V~3.6V;



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Signal	Description
	Lower power mode:1.7V~1.95V
Vcc	Vcc is the power supply line for internal flash memory, its power voltage range is:2.7V~3.6V
VDDi	VDDi is internal power node, not the power supply. Connect 1uF capacitor VDDi to ground
Vss,Vssq	Ground lines.

Note:

NC: No Connect, shall be connected to ground or left floating.

RFU: Reserved for Future Use, must be left floating for future use.

VSF: Vendor Specific Function, must be left floating.



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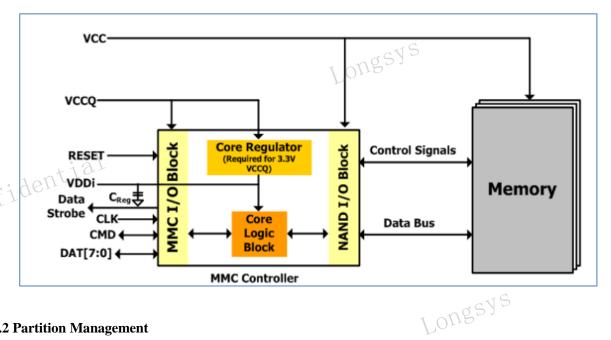




7. Usage Overview

7.1 General description

The eMMC can be operated in 1, 4, or 8-bit mode. NAND flash memory is managed by a controller inside, which manages ECC, wear leveling and bad block management. The eMMC provides easy integration with the host process that all flash management hassles are invisible to the host.



7.2 Partition Management

The embedded device offers also the possibility of configuring by the host additional split local memory partitions with independent addressable space starting from logical address 0x00000000 for different usage models. Default size of each Boot Area Partition is 4096 KB and can be changed by Vendor Command as multiple of 128KB. Boot area partition size is calculated as (128KB * BOOT SIZE MULTI) The size of Boot Area Partition 1 and 2 cannot be set independently and is set as same value Boot area partition which is enhanced partition. Therefore memory block area scan is classified as follows:

- ▶ Factory configuration supplies boot partitions.
- The RPMB partition is 16MB.
- The host is free to configure one segment in the User Data Area to be implemented as enhanced storage media, and to specify its starting location and size in terms of Write Protect Groups. The attributes of this Enhanced User Data Area can be programmed only once during the device life-cycle (one-time programmable).
- Up to four General Purpose Area Partitions can be configured to store user data or sensitive data, or for other host usage models. The size of these partitions is a multiple of the write protect group. Size and attributes can be programmed once in device life-cycle (one-time programmable). Each of the General Purpose Area Partitions can be implemented with enhanced technological features.

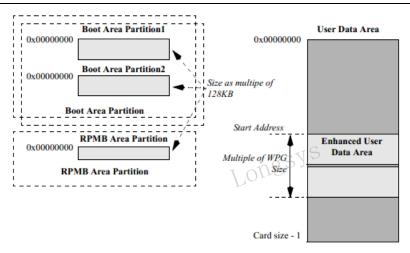
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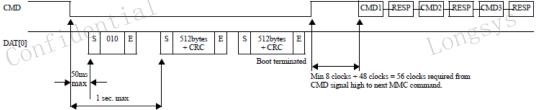
Partitions and user data area configuration

(The size of RPMB area partition is 16MB)

fidential In boot operation mode, the master can read boot data from the slave (device) by keeping CMD line low or sending CMD0 with argument + 0xFFFFFFA, before issuing CMD1. The data can be read from either boot area or user area depending on register setting.

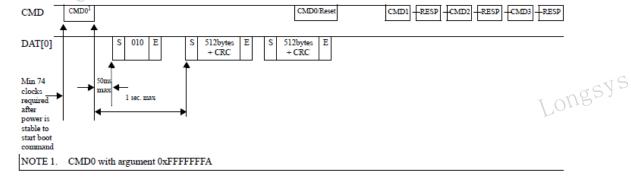
Timing Factor	Value
Boot ACK Time	< 50 ms
Boot Data Time	< 1 s
Initialization Time	< 1 s





State diagram (boot mode)

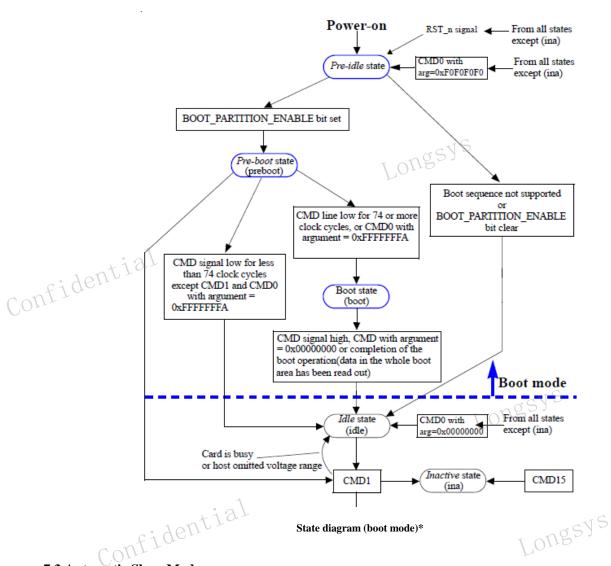




State diagram (alternative boot mode) confiden

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7.3 Automatic Sleep Mode

If host does not issue any command during certain duration, after previously issued command is completed, the device enters "Power Saving mode" to reduce power consumption. At this time, commands arriving at the device while it is in power saving mode will be serviced in normal fashion. The below table explains the condition to enter and exit Auto Power Saving Mode

7.4 Sleep (CMD5)

A card may be switched between a Sleep state and a Standby state by SLEEP/AWAKE (CMD5). In the Sleep state the power consumption of the memory device is minimized. In this state the memory device reacts only to the commands RESET (CMD0 with argument of either 0x000000000 or 0xF0F0F0F0 or H/W reset) and SLEEP/AWAKE (CMD5). All the other commands are ignored by the memory device. The timeout for state transitions between Standby state and Sleep state is defined in the EXT_CSD register S_A_timeout. The maximum current consumptions during the Sleep state are defined in the EXT_CSD registers S_A_VCC_and S_A_VCCQ. Sleep command: The bit 15 as set to 1 in SLEEP/AWAKE (CMD5) argument. A wake command: The bit 15 as set to 0 in SLEEP/AWAKE (CMD5) argument.

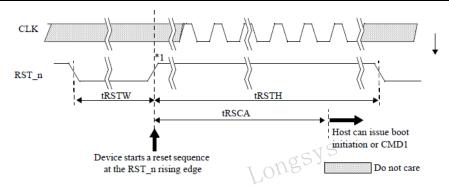
7.5 H/W Reset operation

Device will detect the rising edge of RST_n signal to trigger internal reset sequence

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H/W reset waveform

7.6 High-speed mode selection

After the host verifies that the card complies with version 4.0, or higher, of this standard, it has to enable the high speed mode timing in the card, before changing the clock frequency to a frequency higher than 20MHz. For the host to change to a higher clock frequency, it has to enable the high speed interface timing. The host uses the SWITCH command to write 0x01 to the HS_TIMING byte, in the Modes segment of the EXT_CSD register.

7.7 Bus width selection

After the host has verified the functional pins on the bus it should change the bus width configuration accordingly, using the SWITCH command. The bus width configuration is changed by writing to the BUS_WIDTH byte in the Modes Segment of the EXT_CSD register (using the SWITCH command to do so). After power-on, or software reset, the contents of the BUS_WIDTH byte is 0x00.

7.8 Partition configuration

Model	Area/Partition	Size (GB)	Size (MB)	Size (Sector)	Size (Byte)	Size (Hex, Byte)
	User	28.91	29600	60620800	31037849600	73A000000
FEMDNN032G-	Boot Partition 1	-	4	8192	4194304	400000
A3A55	Boot Partition 2	-	4	8192	4194304	400000
	RPMB	-	16	32768	16777216	1000000

7.9 CID register

The Card Identification (CID) register is 128 bits wide. It contains the card identification information used during the card identification phase (protocol). Every individual flash or I/O card shall have an unique identification number. Every type of ROM cards (defined by content) shall have a unique identification number. The structure of the CID register is defined in the following sections.

Name	Field	Width	CID-slice	CID Value	Remark
Manufacturer ID	MID	8	[127:120]	D6h	
Reserved	-	6	[119:114]		Tongs!
Card/BGA	CBX	2	[113:112]	01h	BGA
OEM/Application ID	OID	8	[111:104]	03h	
Product name	PNM	48	[103:56]	413341353531h	A3A551
Product revision	PRV	8	[55:48]		Not Fixed
Product serial number	PSN	32	[47:16]		Not Fixed
Manufacturing date	MDT	= 1086 II	[15:8]		Not Fixed Not Fixed
	COI_J	1	•		PC





Name	Field	Width	CID-slice	CID Value	Remark
CRC7 checksum	CRC	7	[7:1]		Not Fixed
Not used, always '1'	-	1	[0:0]		

7.10 CSD register

The Card-Specific Data (CSD) register provides information on how to access the card contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register (entries marked by W or E, see below) can be changed by CMD27. The type of the CSD Registry entries coded as follows:

Name	Field	Width	Cell Type	CSD-slice
CSD structure	CSD_STRUCTURE	2	R	[127:126]
System specification version	SPEC_VERS	4	R	[125:122]
Reserved	-	2	R	[121:120]
Data read access-time 1	TAAC	8	R	[119:112]
Data read access-time 2 in CLK cycles (NSAC*100)	NSAC	8	R	[111:104]
Max. bus clock frequency	TRAN_SPEED	8	R	[103:96]
Card command classes	CCC	12	R	[95:84]
Max. read data block length	READ_BL_LEN	4	R	[83:80]
Partial blocks for read allowed	READ_BL_PARTIAL	1 1	ng R	[79:79]
Write block misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]
DSR implemented	DSR_IMP	1	R	[76:76]
Reserved	-	2	R	[75:74]
Device size	C_SIZE	12	R	473:62]
Max. read current @ V _{DD} min	VDD_R_CURR_MIN	3	1 R) 17 E	[61:59]
Max. read current @ V _{DD} max	VDD_R_CURR_MAX	3	R	[58:56]
Max. write current @ V _{DD} min	VDD_W_CURR_MIN	3	R	[55:53]
Iax. write current @ VDD max	VDD_W_CURR_MAX	3	R	[52:50]
Device size multiplier	C_SIZE_MULT	3	R	[49:47]
rase group size	ERASE_GRP_SIZE	5	R	[46:42]
rase group size multiplier	ERASE_GRP_MULT	5	R	[41:37]
Vrite protect group size	WP_GRP_SIZE	5	R	[36:32]
Vrite protect group enable	WP_GRP_MULT	1	R	[31:31]
Manufacturer default ECC	DEFAULT_ECC	2	R	[30:29]
Vrite speed factor	R2W_FACTOR	3	R	[28:26]
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]
artial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]
Reserved	-	4	R	[20:17]
Content protection application	CONTENT_PROT_APP	1	R	[16:16]
File format group	FILE_FORMAT_GRP	1	R/W	[15:15]
Copy flag(OTP)	COPY	1	R/W	[14:14]
	PERM WRITE PROTECT	1	R/W	[13:13]





Name	Field	Width	Cell Type	CSD-slice
Temporary write protection	TMP_WRITE_PROTECT	1	R/W/E	[12:12]
File format	FILE_FORMAT	2	R/W	[11:10]
ECC code	ECC	2	R/W/E	[9:8]
CRC	CRC	7	R/W/E	[7:1]
Not used, always '1'	-	1	-	[0:0]

7.11 Extended CSD registerThe Extended CSD register defines the card properties and selected modes. It is 512 bytes long. The most significant 320 bytes are the Properties segment, which defines the card capabilities and cannot be modified by the host. The lower 192 bytes are the Modes segment, which defines the configuration the card is working in. These modes can be changed by the host by means of the SWITCH command.

Name 121	Field	Size	Туре	Slice [bytes]	Value	Description
100	Reserved	6	-	[511:506]	-	
Extended security error	EXT_SECURITU_ERR	1	R	[505]	Oh	
Supported Command Sets	S_CMD_SET	1	R	[504]	1h	
HPI Features	HPI_FEATURES	1	R	[503]	gSih	
Background operations support	BKOPS_SUPPORT	1	R	[502]	1h	BKOPS supported
Max packed read	MAX_PACKED_READS	1	R	[501]	3Fh	
Max packed write command	MAX_PACKED_WRITES	1	R	[500]	3Fh	SYS
Data Tag Support	DATA_TAD_SUPPORT	1	R	[499]	1h	
Tag Unit Size	TAG_UNIT_SIZE	1	R	[498]	3h	
Tag Resource Size	TAG_RES_SIZE	1	R	[497]	0h	
Context management capabilities	CONTEXT CAPABITILITIES	1	R	[496]	5h	
Large Unit size	LARGE_UNIT_SIZE_M1	1	R	[495]	7h	Large Unit size 8MB
Extended partitions attribute support	EXT_SUPPORT	1	R	[494]	3h	
Supported modes	SUPPORTED_MODES	1	R	[493]	3h	Longs
FFU features	FFU_FEATURES	1	R	[492]	0h	Pous,
Operation codes timeout	OPERATION_CODE_TIMEOU T	1	R	[491]	0h	
FFU Argument	FFU_ARG	4	R	[490:487]	0h	
Barrier support	BARRIER_SUPPORT	1 . 2] R	[486]	0h	
	Reserved	2/177	-	[485:309]	-	
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	Name	Field	Size	Туре	Slice [bytes]	Value	Description		
	CMDQ support	CMDQ_SUPPORT	1	R	[308]	1h			
Ī	CMDQ depth	CMDQ_DEPTH	1	R	[307]	1Fh			
Ī		Reserved	1	-	[306]	-			
	Number of received sectors	NUMBER_OF_RECEIVED_SEC TORS	4	R	[305:302]	Oh			
	Vendor proprietary health report	VENDOR_PROPRIETARY_HE ALTH_REPORT	32	R	[301:270]	Oh			
	Device life time estimation type B	DEVICE_LIFE_TIME_EST_TYP _B	1	R	[269]	Oh			
	Device life time estimation type A	DEVICE_LIFE_TIME_EST_TYP _A	1	R	[268]	1h			
7	Pre EOL information	PRE_EOL_INFO	1	R	[267]	1h			
	Optimal read size	OPTIMAL_READ_SIZE	1	R	[266]	Oh			
	Optimal write size	OPTIMAL_WRITE _SIZE	1	R	[265]	20h			
	Optimal trim unit size	OPTIMAL_TRIM_UNIT_SIZE	1	R	[264]	1h S			
İ	Device version	DEVICE_VERSION	2	R	[263:262]	0h			
	Firmware version	FIRMWARE_VERSION	8	R	[261:254]	-	FW Patch Ver		
	Power class for200MHz, DDR at VCC=3.6V	PWR_CL_DDR_200_360	1	R	[253]	Oh	NS.		
	Cache size	CACHE_SIZE	4	R	[252:249]	10000h)		
	Generic CMD6 timeout	GENERIC_CMD6_TIME	1	R	[248]	Ah	Generic CMD6 timeout 100ms		
	Power-off notification(long) timeout	POWER_OFF_LONG_TIME	1	R	[247]	3Ch	Power off notification(long timeout 600ms		
	Background operations status	BKOPS_STATUS	1	R	[246]	Oh	No operations required		
	Number of correctly programmed sectors	CORRECTLY_PRG_SECTORS_ NUM	4	R	[245:242]	Oh			
	First Initialization time after partitioning	INI_TIMEOUT_AP	1	R	[241]	1Eh	initial time out 3		
	Cache Flushing Policy	CACHE_FLUSH_POLICY	1	R	[240]	0h	Pom		
	Power class for 52Mhz,DDR at 3.6V	PWR_CL_DDR_52_360	1	R	[239]	Oh	rms 100 mA, pea 200 mA		
	Power class for 52Mhz,DDR at 1.95V	PWR_CL_DDR_52_195	entia	R	[238]	0h	rms 65 mA, peal		



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Name	Field	Size	Туре	Slice [bytes]	Value	Description
Power class for 200Mhz at VCCQ=1.95V, VCC=3.6V	PWR_CL_200_195	1	R	[237]	Oh	
Power class for 200Mhz at VCCQ=1.3V, VCC=3.6V	PWR_CL_200_360	1	Lang	SY S [236]	Oh	
Minimum write performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_W_8_52	1	R	[235]	Oh	For cards not reaching the 4.8 MB/s value Only support SDR
Minimum read performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_R_8_52	1	R	[234]	0h	For cards not reaching the 4.8MB/s value
	Reserved	1	-	[233]	-	
TRIM Multiplier	TRIM_MULT	1	R	[232]	0 S5h	trim time out 1.5s
Secure feature support	dential sec_feature_support onfidential	1	R	[231]	Longs 55h	1. Support the secure and insecure trim operations. 2. Support the automatic secure purge operation on retired defective portions of the array. 3. Secure purge operations are supported. 4. Support the sanitize operation
Secure Erase Multiplier	SEC_ERASE_MULT	1	R	[230]	1Bh	secure erase time out 40.5s
Secure TRIM	1	-				secure trim time







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Name	Field	Size	Type	Slice [bytes]	Value	Description
Boot Information	BOOT_INFO	1	R Long	[228] SY ^S	7h	 Support high speed timing boot. Support dual data rate during boot Support alternative boot method
	Reserved	1	-	[227]	-	
Boot partition size	BOOT_SIZE_MULTI	1	R	[226]	20h	boot partition 4096KB
Access size	ACC_SIZE	1	R	[225]	6h	super page 16KB
High-capacity Erase unit size	HC_ERASE_GROUP_SIZE	1	R	[224]	1h	hc erase group size 512KB
High-capacity Erase time out	ERASE_TIMEOU_MULT	1	R	[223]	5h	hc erase time out
Reliable write sector count	REL_WR_SEC_C	1	R	[222]	gS) lh	1 sector
High-capacity write protect group size	HC_WP_GRP_SIZE	1	R	[221]	10h	hc wp group size 8192KB
Sleep current(VCC)	S_C_VCC	1	R	[220]	7h	128μΑ
Sleep current[VCCQ]	s_c_vccq	1	R	[219]	7h	128μΑ
Production state awareness timeout	PRODUCTION_STATE_AWA RENESS_TIMEOUT	1	R	[218]	Lohng	Not defined
Sleep/Awake time out	S_A_TIMEOUT	1	R	[217]	16h	Sleep/Awake timeout 419.43ms
Sleep Notification Time out	SLEEP_NOTIFICATION_TIME	1	R	[216]	10h	Sleep Notification Time out 655.36ms
Sector count	SEC_COUNT	4	R	[215:212]	39D0000h	Depend on capacity
Secure Write Protection Mode	SECURE_WP_INFO	1	R	[211]	1h	
Minimum Write Performance for 8bit @52MHz	MIN_PERF_W_8_52	1	R	[210]	Oh	Long
Minimum Read Performance for 8bit @52MHz	MIN_PERF_R_8_52	1	R	[209]	Oh	
	confid	entli),,	•		1

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Rev. 1.2 FEMDNN032G-A3A55

Name	Field	Size	Туре	Slice [bytes]	Value	Description
Minimum Write Performance for 4bi	t MIN_PERF_W_8_26_4_52	1	R	[208]	Oh	
@52MHz or 8bit @26MHz						
Minimum Read Performance for 4bi @52MHz or 8bit @26MHz	t MIN_PERF_R_8_26_4_52	1	Lang	SY <mark>S</mark> [207]	Oh	
Minimum Write Performance for 4bi @26MHz	t MIN_PERF_W_4_26	1	R	[206]	Oh	
Minimum Read Performance for 4bi @26MHz	t MIN_PERF_R_4_26	1	R	[205]	Oh	
	Reserved	1	-	[204]	-	
Power Class for 26MHz @3.6V	PWR_CL_26_360	1	R	[203]	Oh	rms 100 mA, peak 200 mA
Power Class for 52MHz @3.6V	PWR_CL_52_360	1	R	[202]	18575 Oh	rms 100 mA, peak 200 mA
Power Class for 26MHz @1.95V	PWR_CL_26_195	1	R	[201]	Oh	rms 65 mA, peak
Power Class for 52MHz @1.95V	PWR_CL_52_195	1	R	[200]	Oh	rms 65 mA, peak
Partition switching timing	PARTITION_SWITCH_TIME	1	R	[199]	L Ah 18	Partition switch time out 100ms
Out-of-interrupt bus	OUT_OF_INTERRUPT_TIME	1	R	[198]	5h	HPI time out
I/O Driver Strength	DRIVER_STRENGTH	1	R	[197]	1Fh	
Card Type	CARD_TYPE Ntial	1	R	[196]	57h	HS400 DDR eMMC@200Mhz- 1.8V I/O
	Reserved	1	-	[195]	-	
CSD Structure Version	CSD_STRUCTURE	1	R	[194]	2h	CSD version No.
	Reserved	1	-	[193]	-	
Extended CSD Revision	EXT_CSD_REV	1	R	[192]	8h	Revision 1.8 (for MMC v5.1)
Command Set	CMD_SET	1	R/W/E_P	[191]	0h	
	Reserved	1	-	[190]	-	
Command set revision	CMD_SET_REV	entiz	∫ R	[189]	Oh	
	Reserved 7 10	1	-	[188]	_	1

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Name	Field	Size	Туре	Slice [bytes]	Value	Description
Power class	POWER_CLASS	1	R/W/E_P	[187]	0h	
	Reserved	1	-	[186]	-	
High Speed Interface Timing	HS_TIMING	1	R/W/E_P	[185]	Oh	
Strobe Support	STROBE_SUPPORT	1	R	[184]	1h	
Bus Width Mode	BUS_WIDTH	1	W/E_P O	5 [183]	Oh	
	Reserved	1	Pome	[182]	-	
Erased memory range	ERASE_MEM_CONT	1	R	[181]	Oh	
4	Reserved	1	-	[180]	-	
Partition Configuration	PARTITION_CONFIG	1	R/W/E R/W/E_P	[179]	Oh	
Boot config protection	BOOT_CONFIG_PROT	1	R/W R/W/C_P	[178]	Oh	
Boot bus width1	BOOT_BUS_WIDTH	1	R/W/E	[177]	0h	
	Reserved	1	-	[176]	1	
High-density erase group definition	ERASE_GROUP_DEF	1	R/W/E_P	[175]	g S Oh S	
Boot write protection status registers	BOOT_WP_STATUS	1	R	[174]	Oh	
Boot area write protect register	BOOT_WP	1	R/W R/W/C_P	[173]	Oh	
	Reserved	1	-	[172]	-	VS
User area write	USER_WP	1	R/W R/W/C_P R/W/E_P	[171]	Oh	
	Reserved	1	-	[170]	-	
FW Configuration	FW_CONFIG	1	R/W	[169]	0h	
RPMB Size	RPMB_SIZE_MULT	1	R	[168]	80h	RPMB size is 16MB
Write reliability setting register	WR_REL_SET	1	R/W	[167]	1Fh	
Write reliability parameter register	WR_REL_PARAM	1	R	[166]	15h	Support the enhanced definition of reliable write
Start Sanitize operation	SANITIZE_START	1	W/E_P	[165]	Oh	
Manually start background operations	BKOPS_START	1:18 ont18		[164]	Oh]

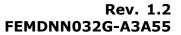
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Rev. 1.2 FEMDNN032G-A3A55

Name		Field	Size	Туре	Slice [bytes]	Value	Description
Enable backgro		BKOPS_EN	1	R/W	[163]	Oh	
H/W reset fund	ction	RST_n_FUNCTION	1	R/W	[162]	0h	
HPI manageme	ent	HPI_MGMT	1	R/W/E_P	[161]	0h	
Partitioning su	pport	PARTITIONING_SUPPORT	1	Long	SYS [160]	7h	Enhanced technological features in partitions and user data area. Device supports partitioning features Device can have extended partition attribute
Max Enhanced	l Area	MAX_ENH_SIZE_MULT	3	R	[159:157]	4D1h	Depend on capacity
Partitions attrib	oute	PARTITIONS_ATTRIBUTE	1	R/W	[156]	Oh	
Partitions setting	ng	PARTITIONS_SETTING_COM PLETED	1	R/W	[155]	Oh	
General Purpose Partition Size	se	GP_SIZE_MULT	12	R/W	[154:143]	Oh	115
Enhanced User Area Size		ENH_SIZE_MULT	3	R/W	[142:140]	Lonne	5 7
Enhanced User Start Address	r Data	ENH_START_ADDR	4	R/W	[139:136]	Oh	
		Reserved	1	-	[135]	-	
Secure Bad Blo Management M		SEC_BAD_BLK_MGMNT	1	R/W	[134]	Oh	
Production state awareness	te (PRODUCTION_STATE_ AWARENESS	1	R/W/E	[133]	Oh	
Package Case Temperature is	;	TCASE_SUPPORT	1	W/E_P	[132]	Oh	
Periodic Wake	-up	PERIODIC_WAKEUP	1	R/W/E	[131]	0h	Long
Program CID/O DDR mode sup		PROGRAM_CID_CSD_DDR_S UPPORT	1	R	[130]	1h	De
		Reserved	2	-	[129:128]	-	
Vendor specifi	c field	VENDOR_SPECIFIC_FIELD	6412	<pre><vendor specfic=""></vendor></pre>	[127:64]	Oh	1
Native sector s	ize	NATIVE_SECTOR_SIZE	1	R	[63]	Oh	Ţ

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	Name	Field	Size	Туре	Slice [bytes]	Value	Description
Se	ector size emulation	USE_NATIVE_SECTOR	1	R/W	[62]	0h	
Se	ector size	DATA_SECTOR_SIZE	1	R	[61]	0h	
1s	st initialization after						
di	sabling sector size	INI_TIMEOUT_EMU	1	R	[60]	0h	
en	nulation						
Cl	lass 6 commands	CLASS C CTDI	1	D WY/EOD	SY 5 [59]	0h	
co	ontrol	CLASS_6_CTRL	1	R/W/E_P	[39]	On	
N	umber of addressed	DYNCAP_NEEDED	1	R	[58]	0h	
gr	oup to be Released	DINCAF_NEEDED	1	K	[56]	OII	
Ex	xception events	EXCEPTION_EVENTS_CTRL	2	R/W/E_P	[57:56]	0h	
co	ontrol	EACEI HON_EVENIS_CIRE	L	K/ W/E_I	[37.30]	OII	
Ex	xception events	EXCEPTION_EVENTS_STAT	2	R	[55:54]	0h	
sta	atus	US	L	K	[33.34]	OII	
Ex	xtended Partitions	EXT_PARTITIONS_ATTRIBU	2	R/W	[53:52]	0h	
A	ttribute	TE	2	IX/ VV	[33.32]	OII	
Co	ontext configuration	CONTEXT_CONF	15	R/W/E_P	[51:37]	0h	
Pa	acked command	PACKED_COMMAND_STAT	1	R	[36]	Oh C	
sta	atus	US	1	K	[30]	25 9 S	
Pa	acked command	DACKED EARLINE INDEV	1	R	[35]	0h	
fa	ilure index	PACKED_FAILURE_INDEX	1	K	[55]	On	
Po	ower Off	POWER_OFF_NOTIFICATIO	1	R/W/E_P	[34]	0h	
N	otification	N	1	R/W/E_F	[34]	OII	
Co	ontrol to turn the	ON/OFF CACHE_CTRL	1	R/W/E P	[33]	0h	-1 C
Ca	ache ON/OFF	ONOFF CACHE_CIRL	1	K/W/E_P	[55]	1 008	SYS
Fl	lushing of the cache	FLUSH_CACHE	1	W/E_P	[32]	Oh	
Co	ontrol to turn the	ON/OFF BARRIER_CTRL	1	R/W	[21]	Ob	
Ва	arrier ON/OFF	ON/OFF BARRIER_CIRL	1	K/W	[31]	0h	
М	lode config	MODE_CONFIG	1	R/W/E_P	[30]	0h	
М	lode operation codes	MODE_OPERATION_CODES	1	W/E_P	[29]	0h	
		Reserved dell	2	-	[28:27]	-	
FI	FU status	FFU_STATUS	1	R	[26]	0h	
Pr	re loading data size	PRE_LOADING_DATA_SIZE	4	R/W/E_P	[25:22]	0h	
M	lax pre loading data	MAX_PRE_LOADING_DATA		1	524 407		
siz	ze	_SIZE	4	R	[21:18]	-	
Pr	roduct state	DD ODLIGH CHARE AWADEN					
av	vareness	PRODUCT_STATE_AWAREN	1	R/W/E&R	[17]	0h	Long
en	nablement	ESS_ENABLEMENT					Do
~	n	GEOLDE DEMONAL TUDE		D/MIOS	F1 62	01	
Se	ecure Removal Type	SECURE_REMOVAL_TYPE	1	R/W&R	[16]	9h	
Co	ommand Queue	G.D. M	_	1,,,,,,,			
M	Iode Enable	CMDQ_MODE_EN	ntie	R/W/E_P	[15]	Oh	1
		Reserved £10	15	-	[14:0]	-	1

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Notes:

R= Read-only

R/W=One-Time Programmable and readable

R/W/E=Multiple writable with value kept after a power cycle, assertion of the RST_n signal, and any CMD0 reset, and readable TBD=To Be Defined.

Reserved bits should be read as 0.





7.12 OCR Register

The 32-bit operation conditions register stores the VCCQ voltage profile of the eMMC. In addition, this register includes a status information bit. This status bit is set if the eMMC power up procedure has been finished. The OCR register shall be implemented by eMMC.

OCR bit	VCCQ voltage window	eMMC
[6:0]	Reserved	000 0000Ь
[7]	1.7–1.95	1b
[14:8]	2.0–2.6	000 0000Ь
[23:15]	2.7–3.6	1 1111 1111b
[28:24]	Reserved	000 0000Р
[30:29]	Access Mode	00b (byte mode)/10b (sector mode)
[31]	power up status bit (busy)*	

Note*: This bit is set to LOW if the eMMC has not finished the power up routine. The supported voltage range is coded as shown in table.

7.13 Field firmware update(FFU)

In order to download a new firmware, the Longsys requires instruction sequence following JEDEC standard.

Longsys FFU only supports Manual mode (MODE_OPERATION_CODES is not supported). For more details, see as the following. Flow and register table given below.

Longsys eMMC Field F/W update flow - CMD sequence

Operation	CMD	Remark	
Set block length 512B	CMD16, arg: 0x00000200		i S
Enter FFU mode	CMD6, arg: 0x031E0100	1 ong5	3
Send FW to	CMD 24/25 are a 0x/00000000	Send FW data after CMD24/ CMD25, Argument must be	
device(Download)	CMD 24/25, arg : 0x00000000	FFU_ARG.	
CMD12 : Stop	CMD12, arg: 0x000000000	If send CMD24,this step is not needed.	
CMD6: Exit FFU mode	CMD6, arg: 0x031E0000	1	
Check if FFU is succeeded	CMD9 are a 0200000000	Check EXT_CSD[26]: FFU_SUCCESS	CVS
Check if FFO is succeeded	CMD8, arg: 0x00000000	If FFU_SUCCESS is 0, FFU is succeeded, otherwise FFU is	ngsys
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		failed.
CMD0/HW Reset/Power cycle	Reset to change the FW	
Re-Init to trans state	CMD0, CMD1	

SUPPORTED_MODE[493] (Read Only)

BIT[0]: '0' FFU is not supported by the device.

'1' FFU is supported by the device.

BIT[1]: '0' Vendor specific mode (VSM) is not supported by the device.

'1' Vendor specific mode is supported by the device.

Bit	Field	Supportability
Bit[7:2]	Reserved	-
eiden Bit[1]	VSM	Support
Bit[0]	FFU	Support

FFU_FEATURE[492] (Read Only)

BIT[0]: '0' Device does not support MODE OPERATION CODES field (Manual mode)

'1' Device supports MODE OPERATION CODES field (Auto mode)

Bit	Field	Supportability
Bit[7:1]	Reserved	-
Bit[0]	SUPPORTED_MODE_OPERATION_CODES	Not support

FFU_ARG[490-487] (Read Only)

Using this field the device reports to the host which value the host should set as an argument for read and write commands in FFU mode.

FW_CONFIG[169] (R/W)

BIT[0]: Update disable

0x0 : FW updates enabled.

0x1 : FW update disabled permanently

Bit cide!	Field	Supportability
Bit[7:1]	Reserved	-
Bit[0]	Update disable	FW updates enabled (0x0)

FFU_STATUS[26] (R/W/E_P)

FU_STATUS[26] (R/W/E_P)	
Using this field the device reports to the host the state of FFU process	Iongsy
Value	Description
0x13 ~ 0xFF	Reserved
0x12	Error in downloading Firmware
0x11	Firmware install error
0x10 1 2 1 2 1 2 1	General error
$0x01 \sim 0x0F$	Reserved 101



0x00	Success

OPERATION_CODES_TIMEOUT[491](Read Only)

Maximum timeout for the SWITCH command when setting a value to the MODE_OPERATION_CODES field. The register is set to '0', because the controller doesn't support MODE_OPERATION_CODES.

Value	Description	Timeout value
$0x01 \sim 0x17$	MODE_OPERATION_CODES_TIMEOUT = 100us x	(Not defined)
	20PERATION_CODES_TIMEOUT	
0x18 ~ 0xFF	Reserved	-

MODE_OPERATION_CODES[29] (W/E_P)

The host sets the operation to be performed at the selected mode, in case MODE_CONFIGS is set to FFU_MODE_OPERATION_CODES could have the following values:

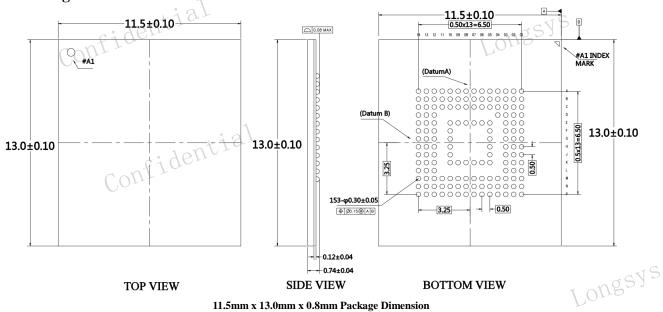
eiden	Value	Description
	0x01	FFU_INSTALL
	0x02	FFU_ABORT
	0x00, others	Reserved

7.14 S.M.A.R.T. Health Report

Col

S.M.A.R.T. is a monitoring system that detects and reports on various indicators of eMMC reliability (Including original bad blocks, increased bad blocks, power-up number, power-loss counts and etc), with the intent of enabling the anticipation of hardware failures. We may be able to use recorded S.M.A.R.T. data to discover where the faults lie, ensure how to solve the problems and prevent them from recurring in future eMMC designs (For details, please refer to app note).

8. Package Dimension









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9 Connection Guide

9.1 Schematic Diagram

- > Coupling capacitor should be connected with VCC/VCCQ and VSS as closely as possible.
- The resistance on the CLK line is highly recommended (0Ω by default). 0Ω ~100Ω is also available.
- ➤ LONGSYS recommends to separate VCC and VCCQ power.
- ➤ VDDi Capacitor is min 0.1uF.
- LONGSYS recommends lay the VSS between the CLK and the Data lines.

The resistance on the CLK line is highly recommended (0 Ω by default)

10. Processing Guide

It is recommended to follow the instructions of Moisture Sensitivity Level 3.

In the case of Pre-program before SMT, It is highly recommended to limit the size of data pre-programmed to the eMMC, please contact your agency for more information.

- > The amount of data pre-programmed (data written before SMT) is limited, it should be managed properly.
- Maximum size for the data-written to IDA.

Part Number	Size limited for Pre-programmed Data
FEMDNN032G-A3A55	9.5GB
(,011-	

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MTFC32GAPALBH-IT MTFC8GACAALT-4M IT THGBMNG5D1LBAIT MTFC4GACAALT-4M IT GLS85VM1004G-S-I-BZYE-ND233
GLS85VM1004G-S-I-LFWE-ND232 GLS85VM1016C-M-I-BZYE-ND231 SDINBDG4-8G-ZA2 MTFC32GAZAQDW-AAT SDINBDG48G-XA2 SDINBDG4-16G-ZA2 S40FC004C1B2I00300 FEMDRW008G-88A39 FEMDRM008G-58A39 FEMDNN064G-A3A56
FEMDNN016G-58A46 FEMDME016G-A8A43 FEMDRM016G-58A43 FEMDRM032G-A3A55 FEMDMW008G-88A39 FEMDME008GA8A39 FEMDMW032G-88A19 SDINBDG4-16G SDINBDG4-8G SDINBDG4-8G-XI1 SDINBDG4-8G-I1 SDINBDG4-16G-I1
SDINADF4-16G-H SDINBDG4-32G SDINBDG4-8G-ZA SDINBDG4-64G-II SDINBDG4-32G-ZA SDINBDG4-32G-XA
THGBMNG5D1LBAIL SDINBDG4-64G-XI1 SDINBDG4-64G-XA SDINBDG4-8G-XA SDINBDG4-32G-XI1
SDINBDG4-16G-XA SDINBDA4-32G SDINBDG4-32G-I1 SDINBDG4-64G SDINBDG4-64G-ZA ASFC8G31M-51BIN ASFC4G31M51BIN FEMDNN032G-A3A55 GLS85VM1032C-M-I-BZYE-ND231 GLS85VM1008Q-S-I-BZYE-ND235 GLS85VM1008E-S-I-BZYE-ND237